

Electronics for IoT

Semiconductors

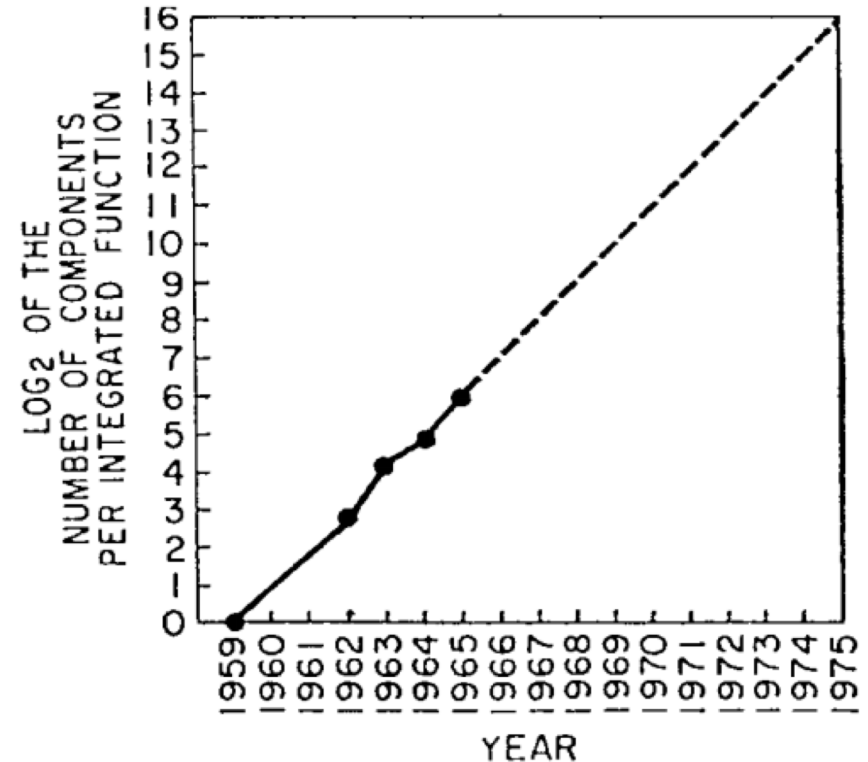
Bernhard E. Boser
University of California, Berkeley
boser@eecs.berkeley.edu

Moore's Law

Cramming More Components onto Integrated Circuits

GORDON E. MOORE, LIFE FELLOW, IEEE

Electronics, April 19, 1965

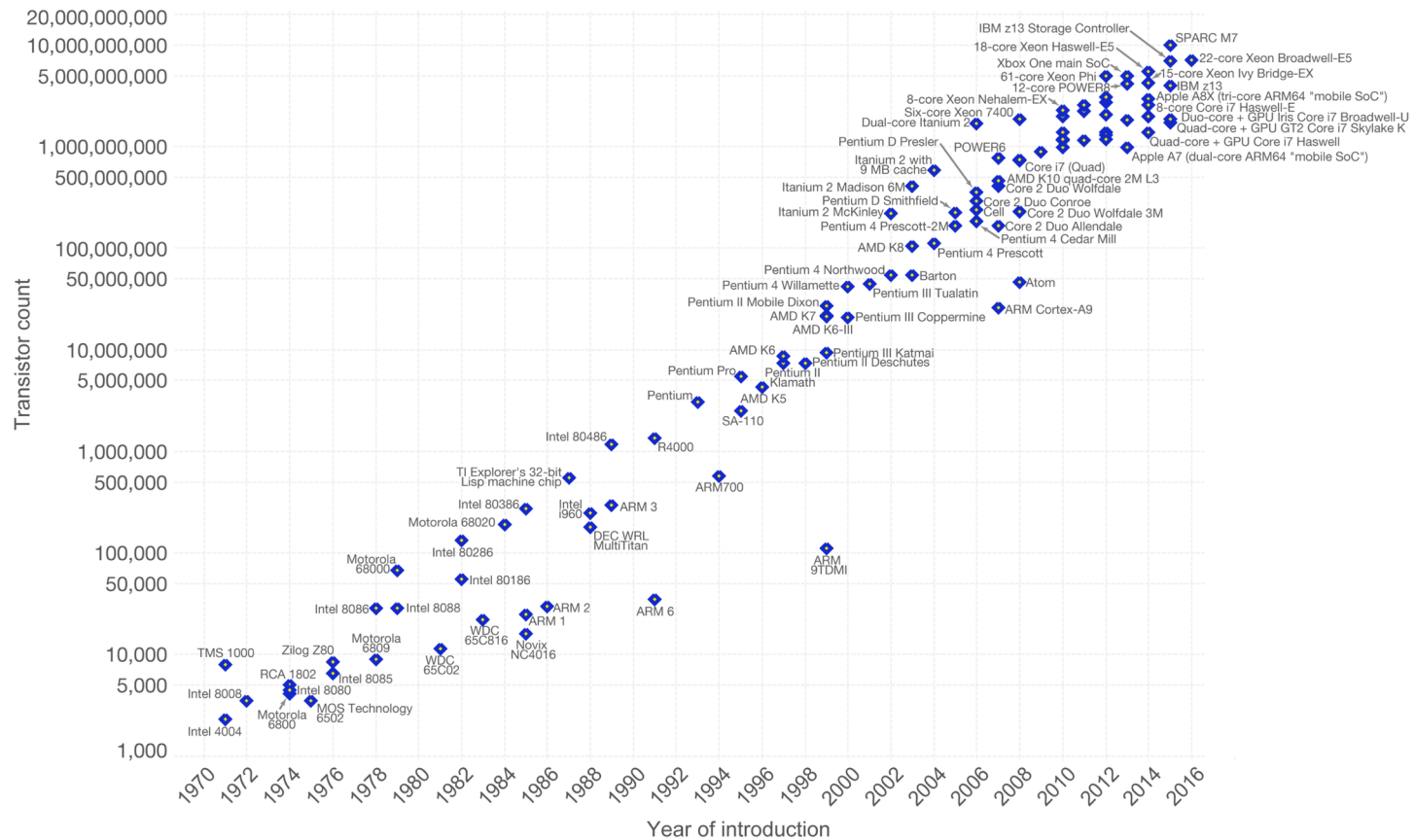


Number of Transistors

Moore's Law – The number of transistors on integrated circuit chips (1971-2016)



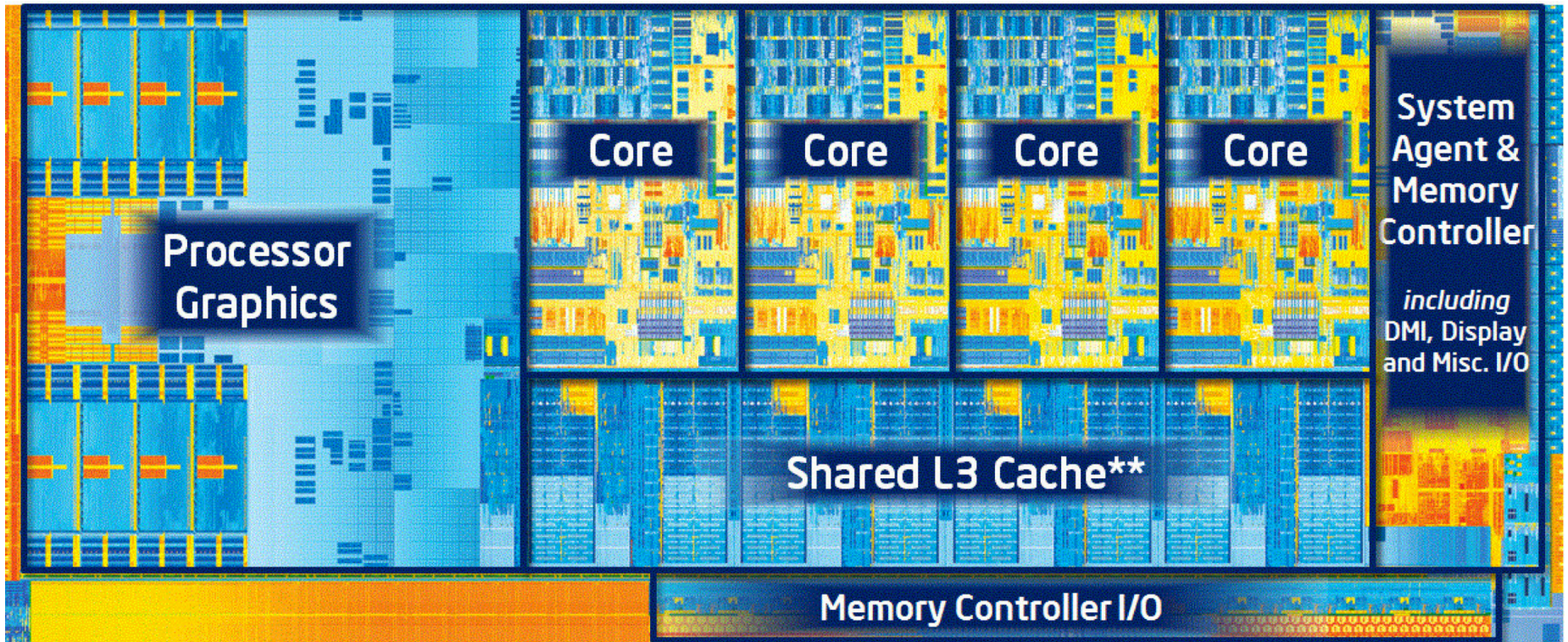
Moore's law describes the empirical regularity that the number of transistors on integrated circuits doubles approximately every two years. This advancement is important as other aspects of technological progress – such as processing speed or the price of electronic products – are strongly linked to Moore's law.



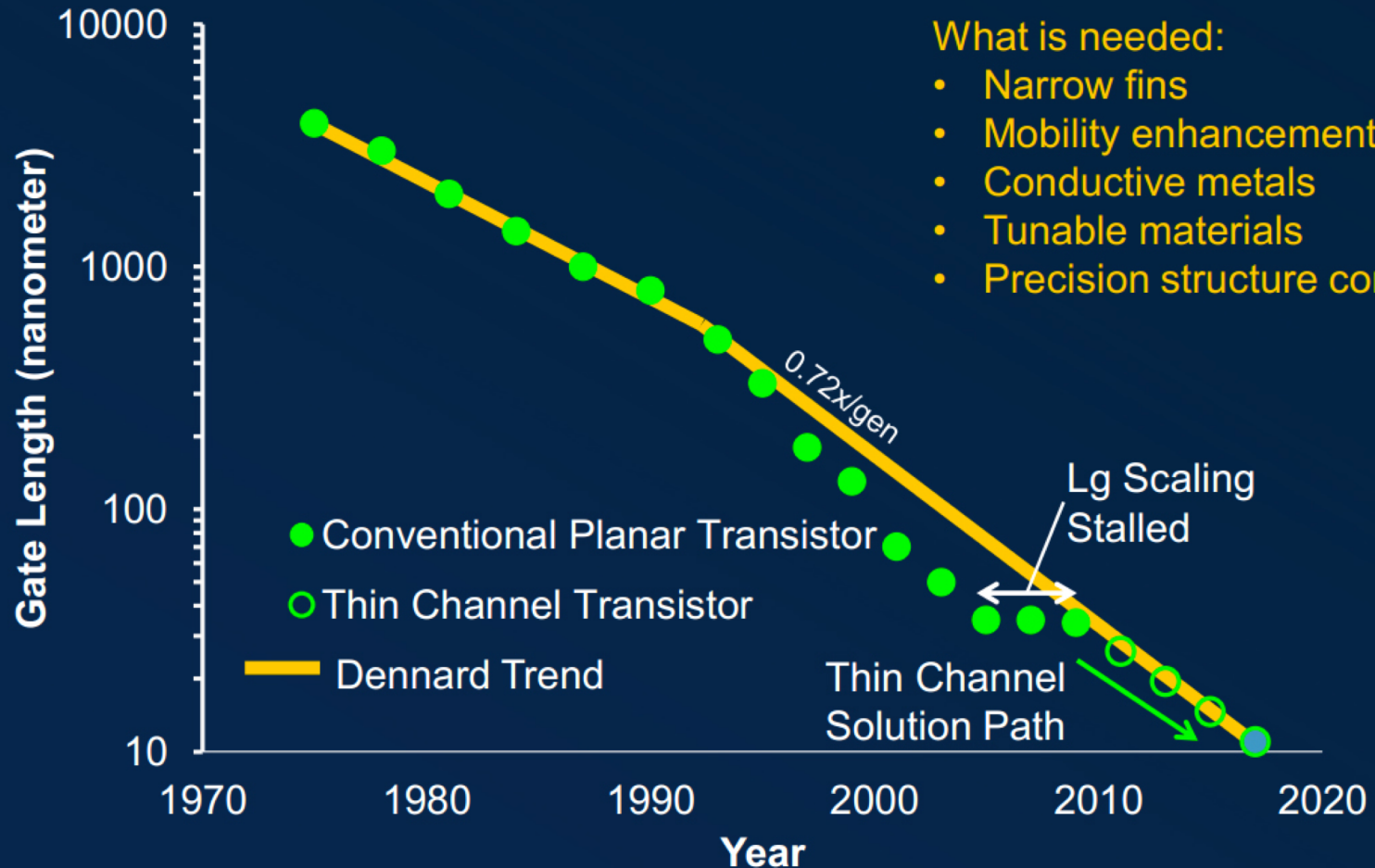
Data source: Wikipedia (https://en.wikipedia.org/wiki/Transistor_count)
 The data visualization is available at [OurWorldinData.org](https://ourworldindata.org). There you find more visualizations and research on this topic.

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Processor



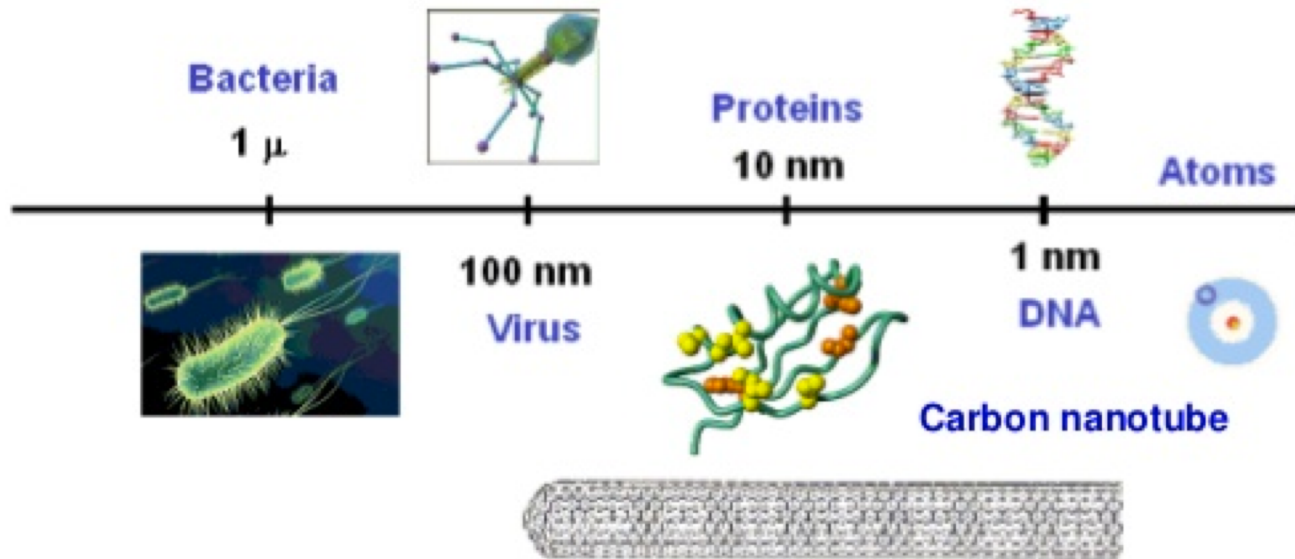
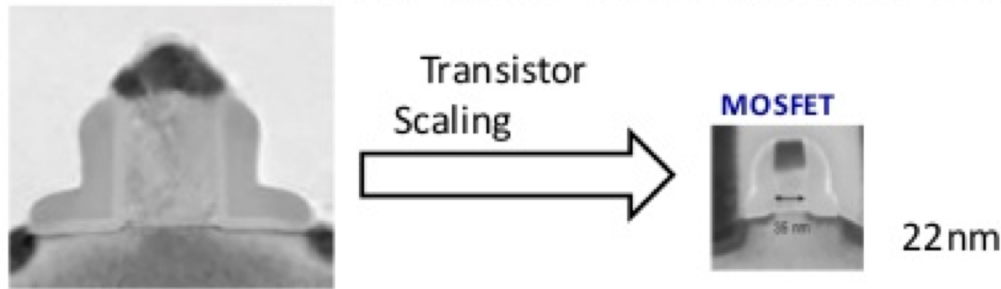
Continue The Lg Scaling Path



What is needed:

- Narrow fins
- Mobility enhancement
- Conductive metals
- Tunable materials
- Precision structure control

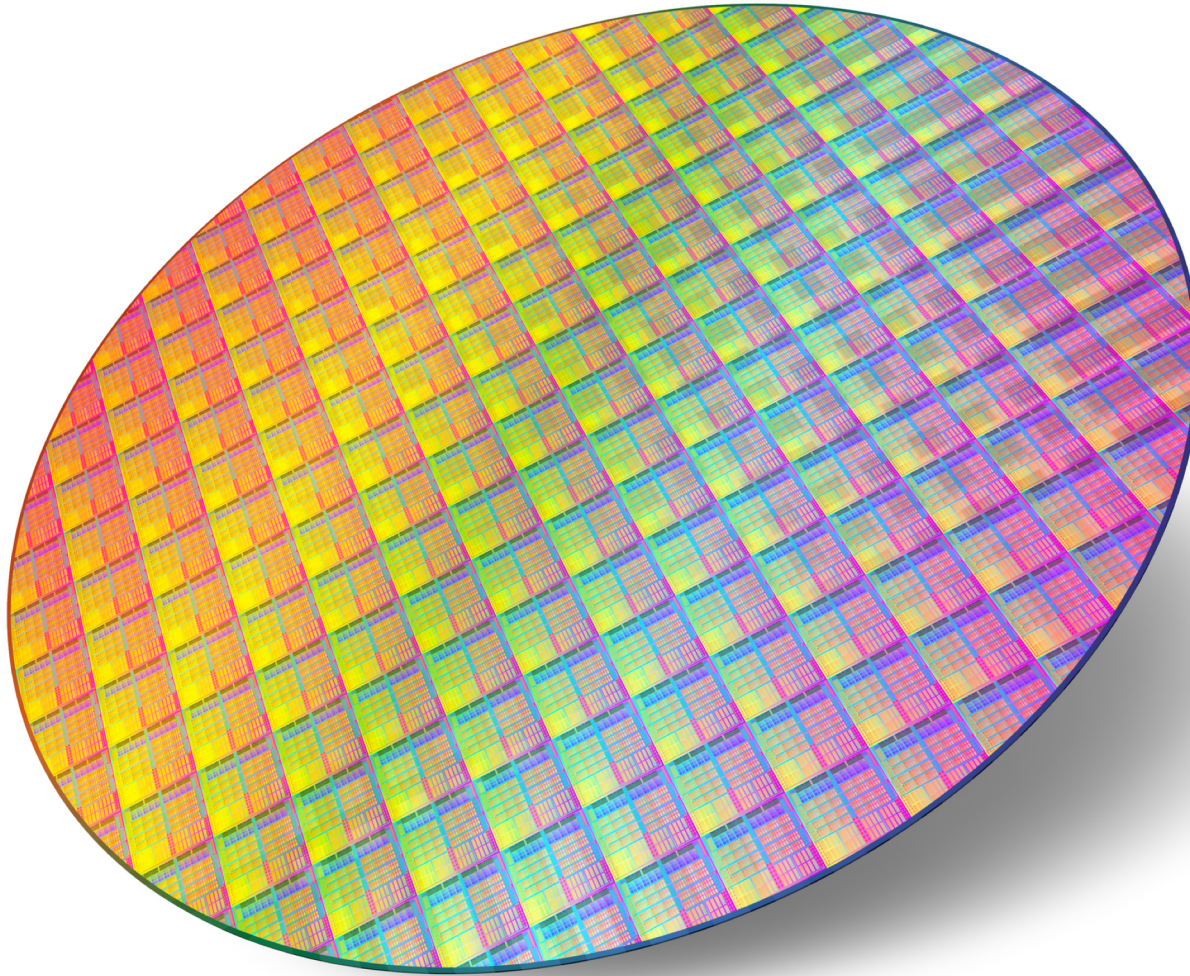
The Nanometer Size Scale



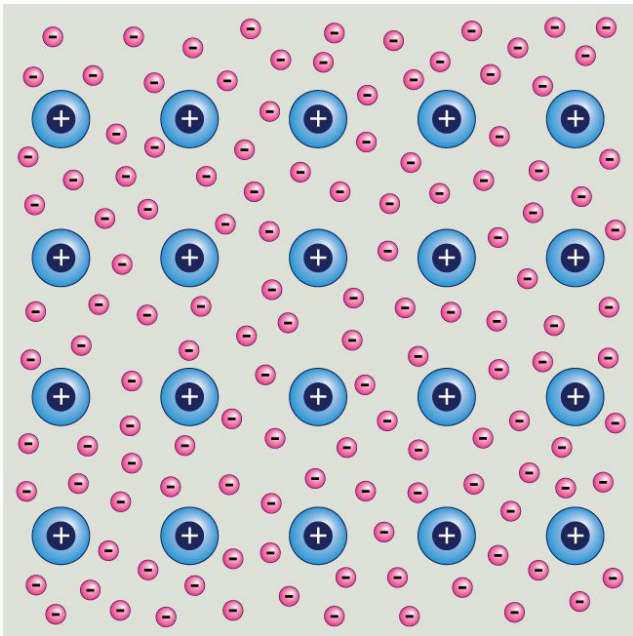
Scaling cannot go on forever because transistors cannot be smaller than atoms

Yield

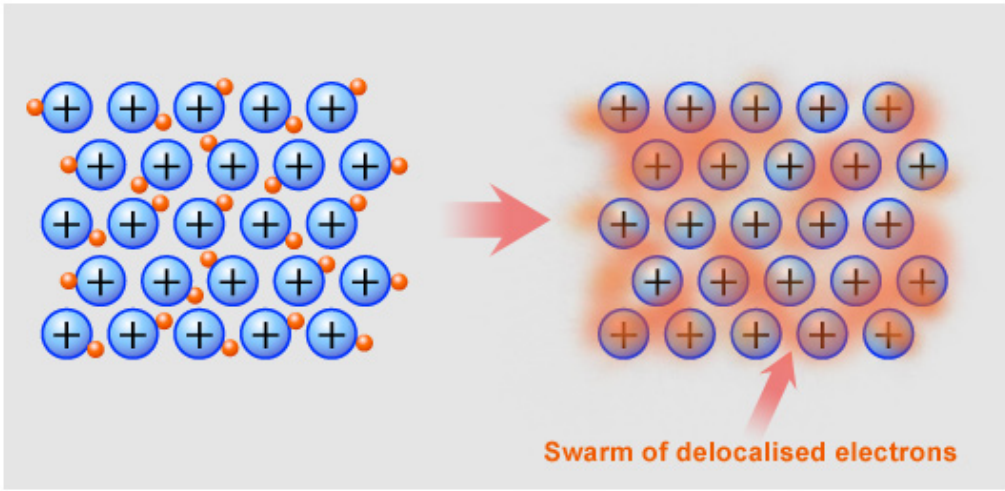
Silicon Wafer



Metals



Metallic Bonding

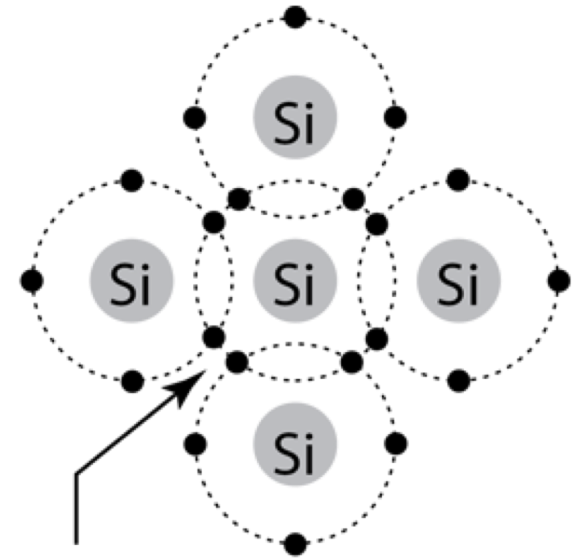


The diagram illustrates the process of metallic bonding. On the left, several blue spheres with plus signs (+) are shown, each with a few small orange spheres (representing valence electrons) attached to its outer surface. A red arrow points to the right, where the spheres are now arranged in a regular grid. The orange spheres are no longer attached to individual atoms but are instead spread out and shared among all the atoms, forming a 'swarm of delocalised electrons'. A red arrow points to this swarm with the label 'Swarm of delocalised electrons'.

The outer electrons are so weakly bound to metal atoms that they are free to roam across the entire metal. Having 'lost' their outer electrons, individual metal atoms are more like positive ions in a swarm of communal electrons.

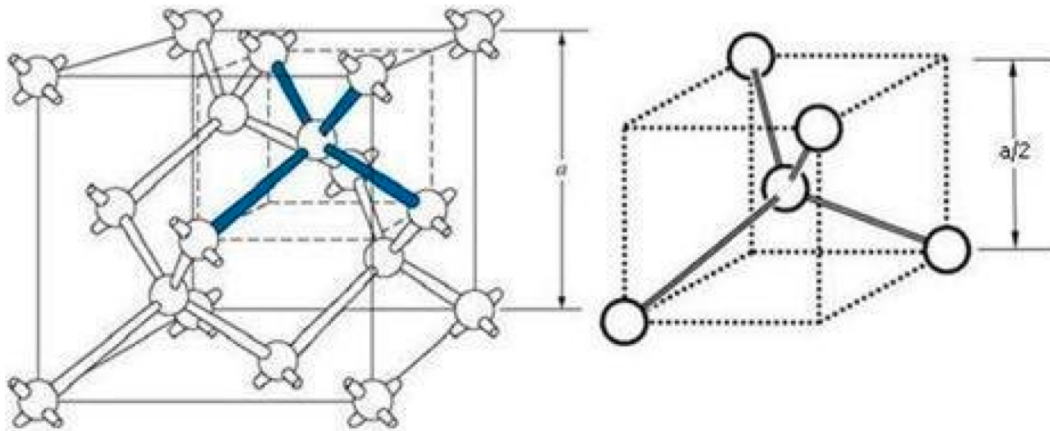
Insulators

Semiconductors



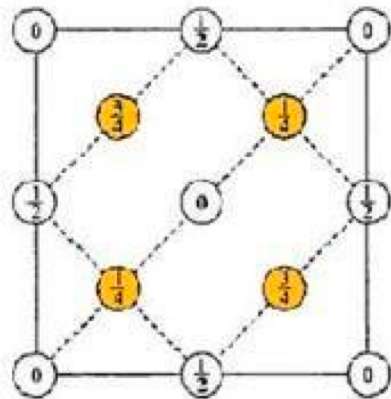
Shared electrons
of a covalent
bond.

Lattice Constant



(a)

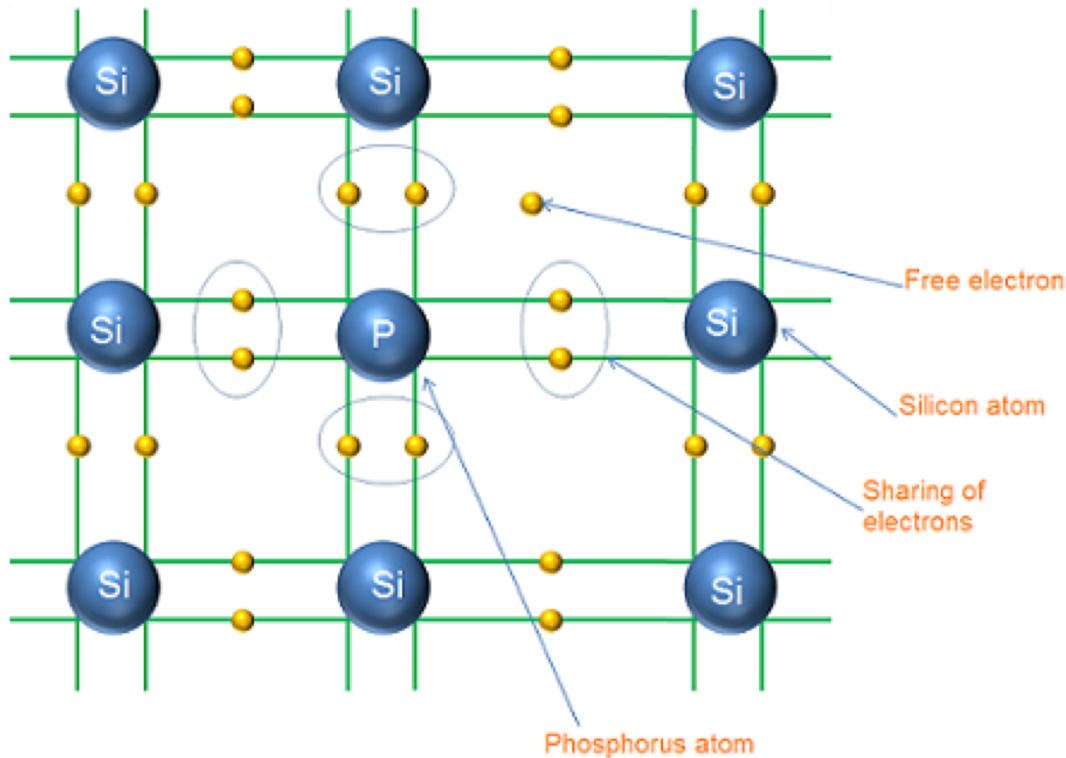
(b)



(c)

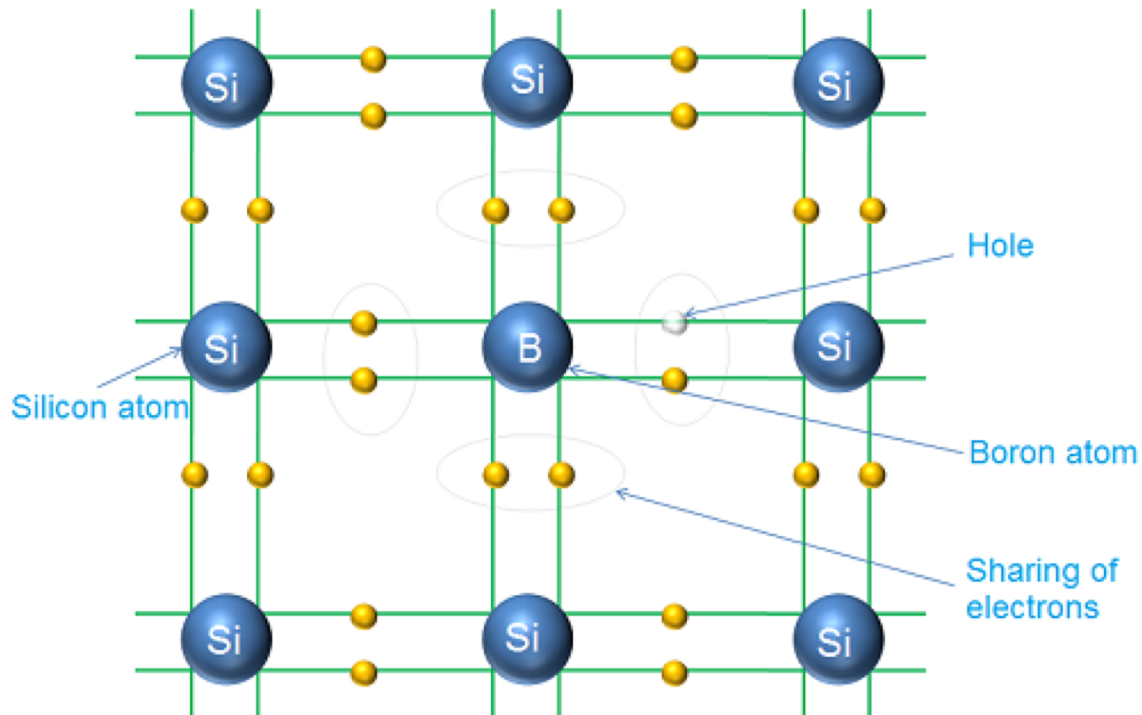
Material	Lattice constant (Å)
C (diamond)	3.567
C (graphite)	$a = 2.461$ $c = 6.708$
Si	5.431
Ge	5.658
AlAs	5.6605
AlP	5.4510
AlSb	6.1355
GaP	5.4505
GaAs	5.653
GaSb	6.0959
InP	5.869

N-type Semiconductors



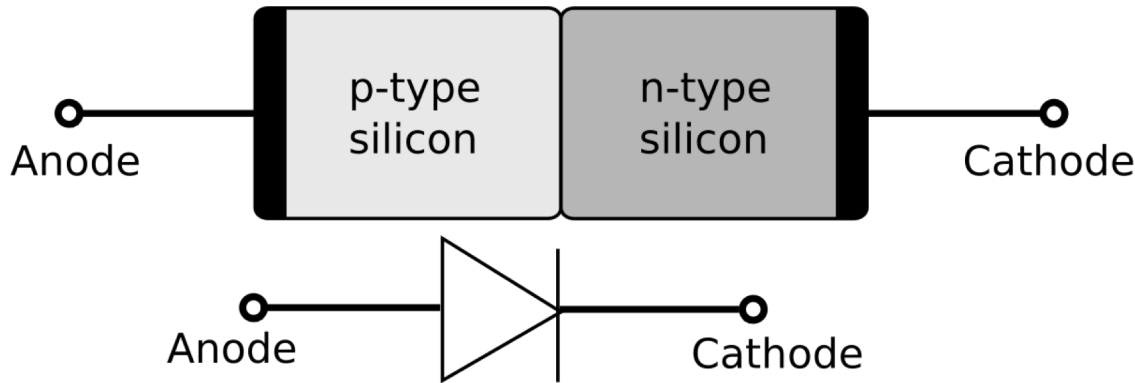
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P-type Semiconductors

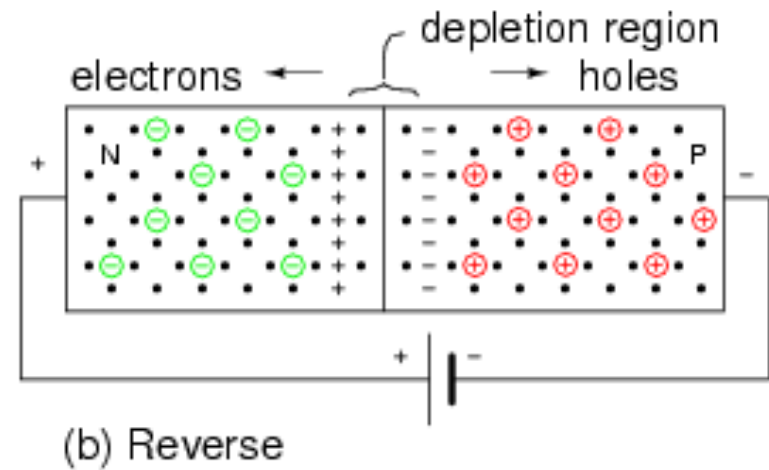
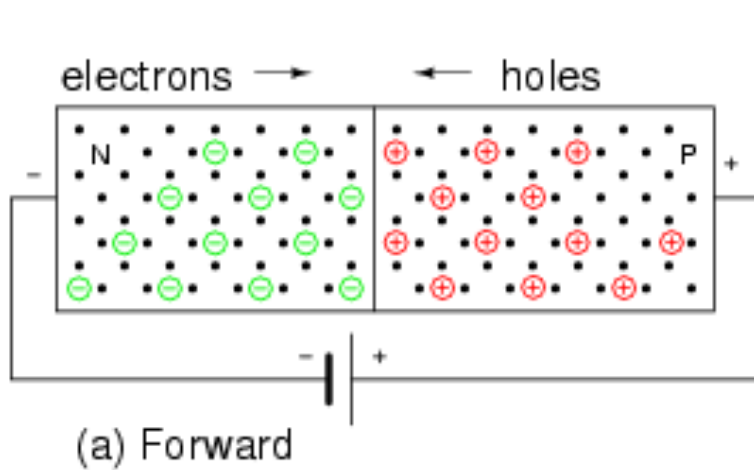
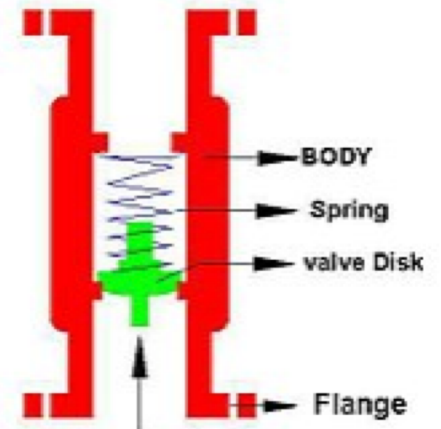


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Diodes



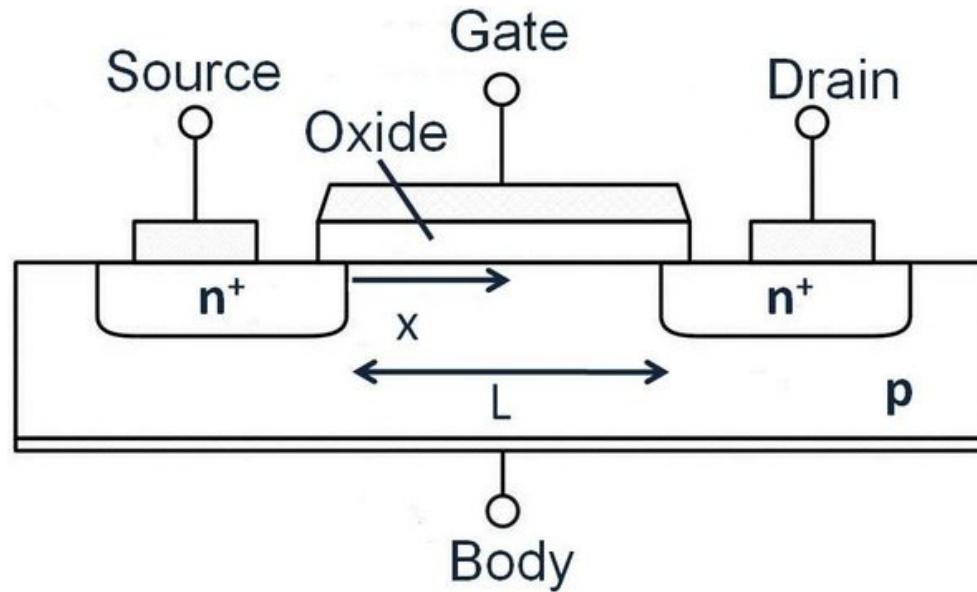
Vertical check valve



Field Effect Transistor (FET)

MOSFET

Metal Oxide Semiconductor FET



Switch Logic – Example: Adder

Switch Logic

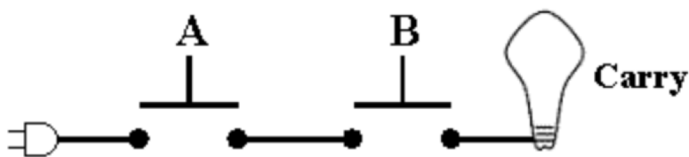
Building an Adder with Switches

Now that you are comfortable adding binary numbers together, let's see how we could make an adding machine using transistors. We will use simple light switches here to make things clearer—but this is not an oversimplification: the transistor logic works very similarly. For this example, we will build part of an adding machine that can add two binary digits (bits) together.

Here are the possible answers obtained from adding two bits:

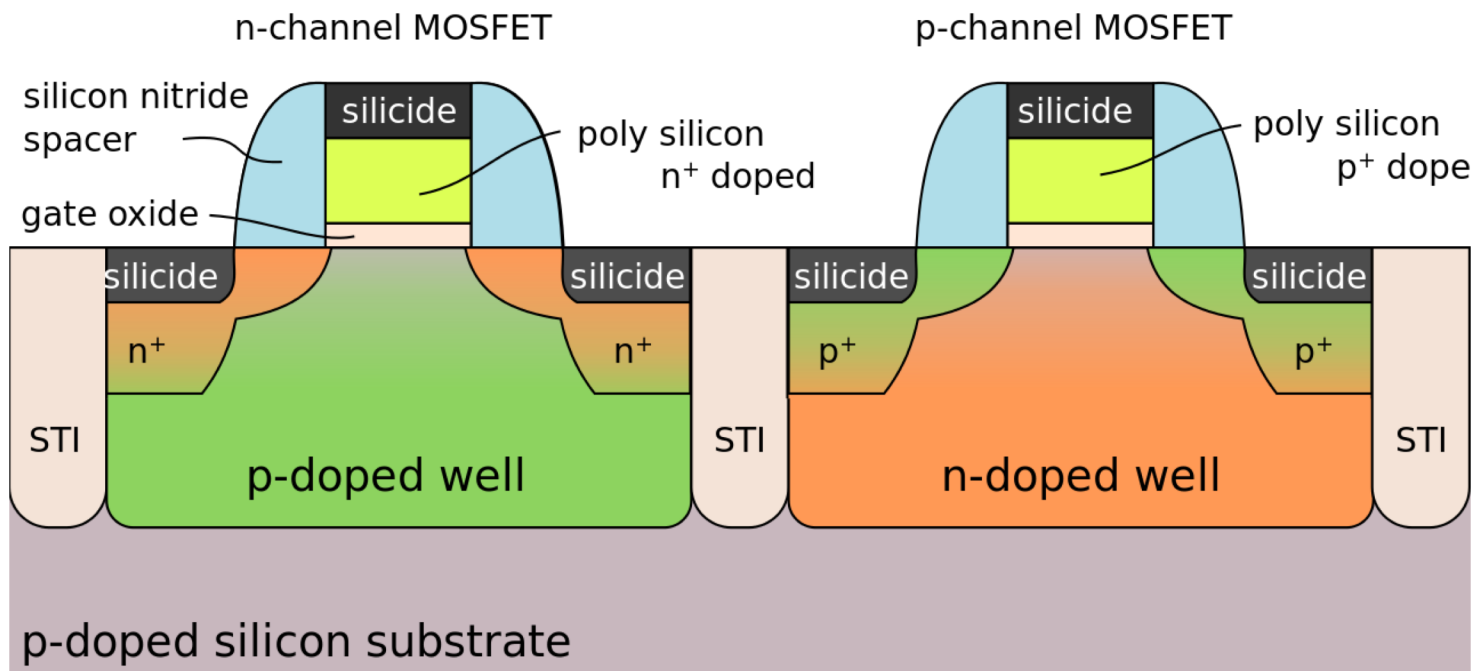
A	B	Carry	Sum
0	0	0	0
0	1	0	1
1	0	0	1
1	1	1	0

We'll just design the "Carry" output of the adder here (the Sum is a bit harder, but also can be done using only transistor switches). The Carry is 1 only if both of our inputs are 1. That is, the Carry is 1 when input A **AND** input B are 1. Thus we can use two switches in a row just as shown above to build the Carry output of our adding machine.



Using combinations of transistor switches, we can build circuits to add, subtract, multiply, and divide. We can also use them to make very simple decisions, by using the logical **AND** or the logical **OR** functions.

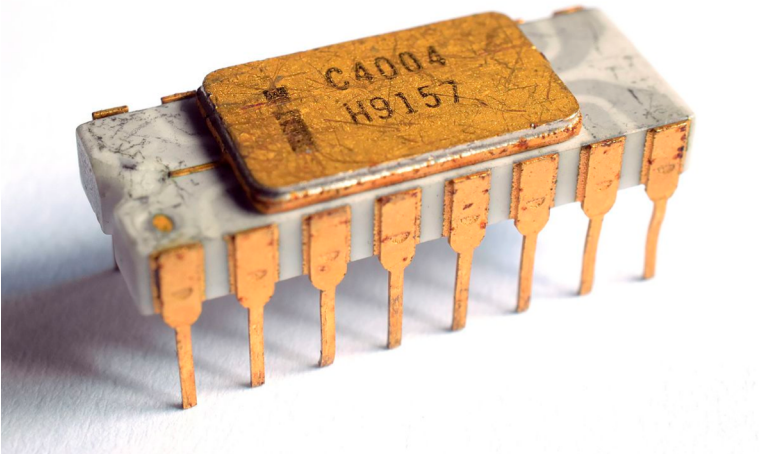
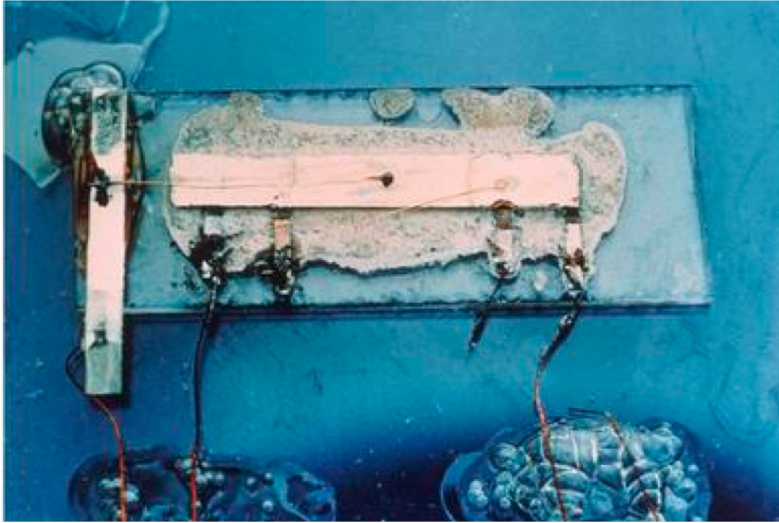
CMOS



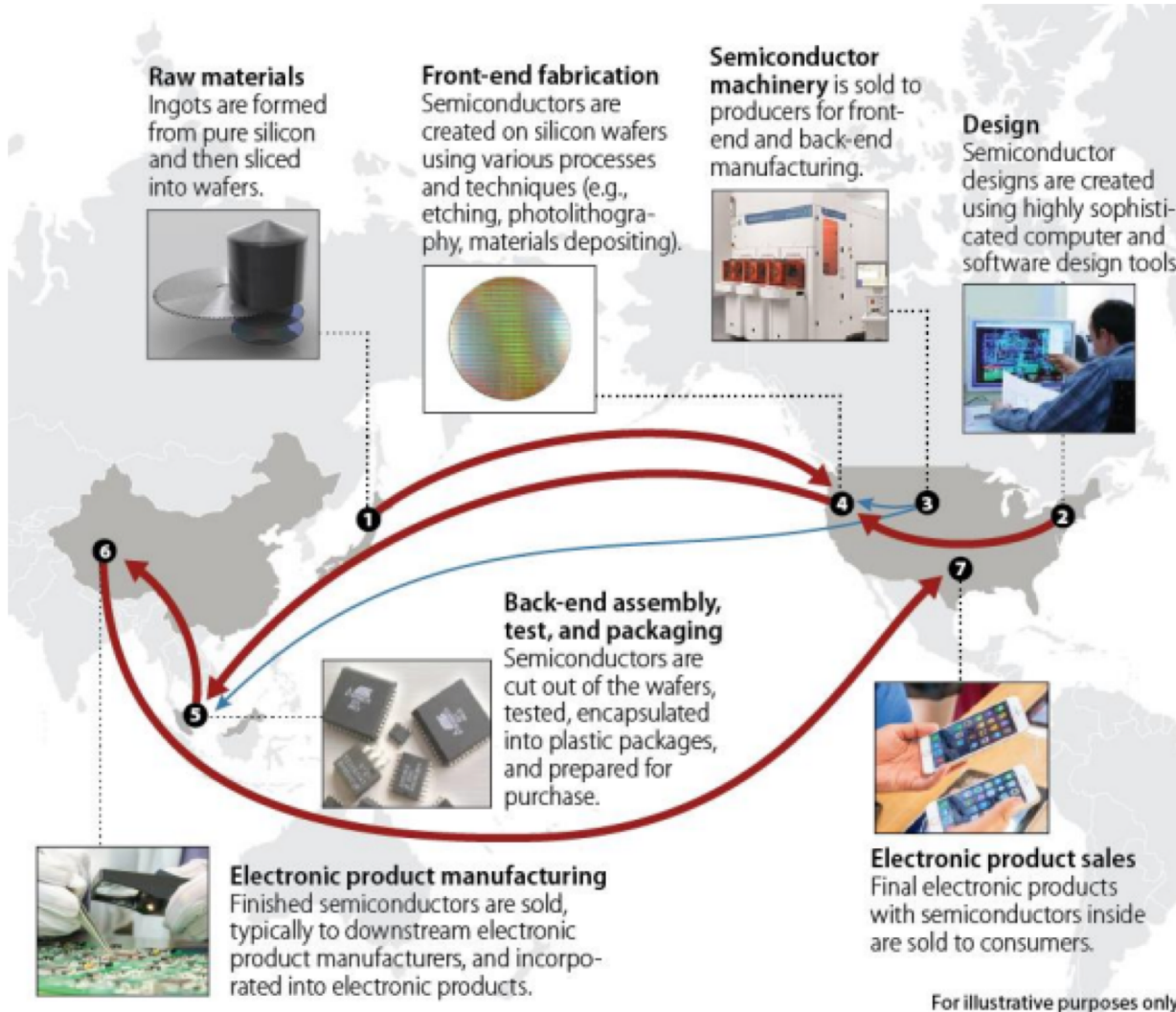
Acronyms

- Transistor
 - Semiconductor device
- Field Effect Transistor (FET)
 - Specific physical implementation
 - Alternative: Bipolar Junction Transistor (BJT)
- Metal Oxide FET (MOSFET)
 - Particular realization of FET
- NMOS, PMOS
 - Types of MOSFET transistors
- CMOS
 - Process capable of fabricating NMOS and PMOS FETs

Batch Fabrication



Semiconductor Production

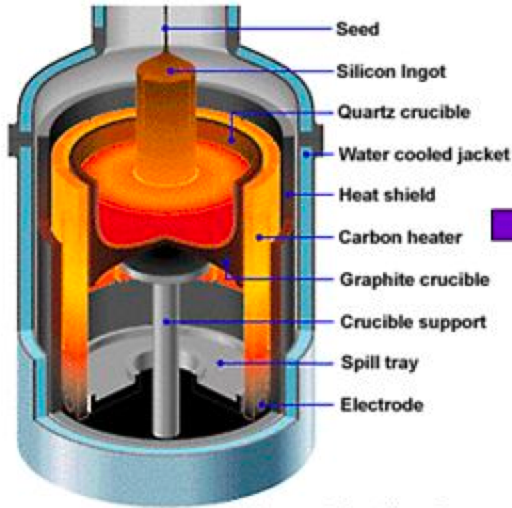


IC Fabrication Overview

Procedure of Silicon Wafer Production



Raw material — Polysilicon nuggets purified from sand

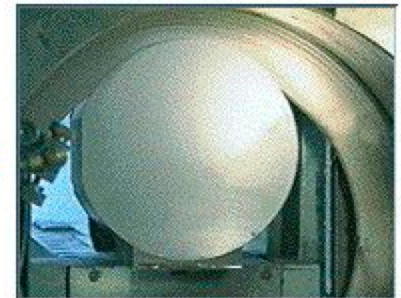


Cz crystal pulling furnace

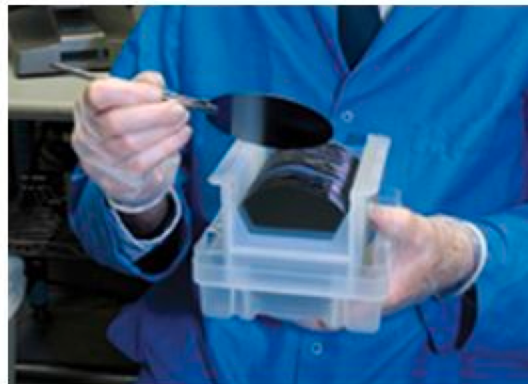
Crystal pulling



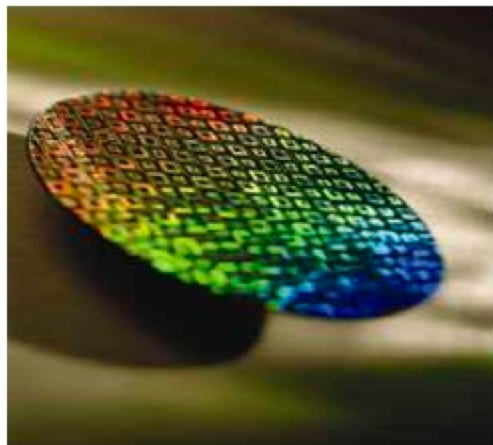
Si crystal ingot



Slicing into Si wafers using a diamond saw

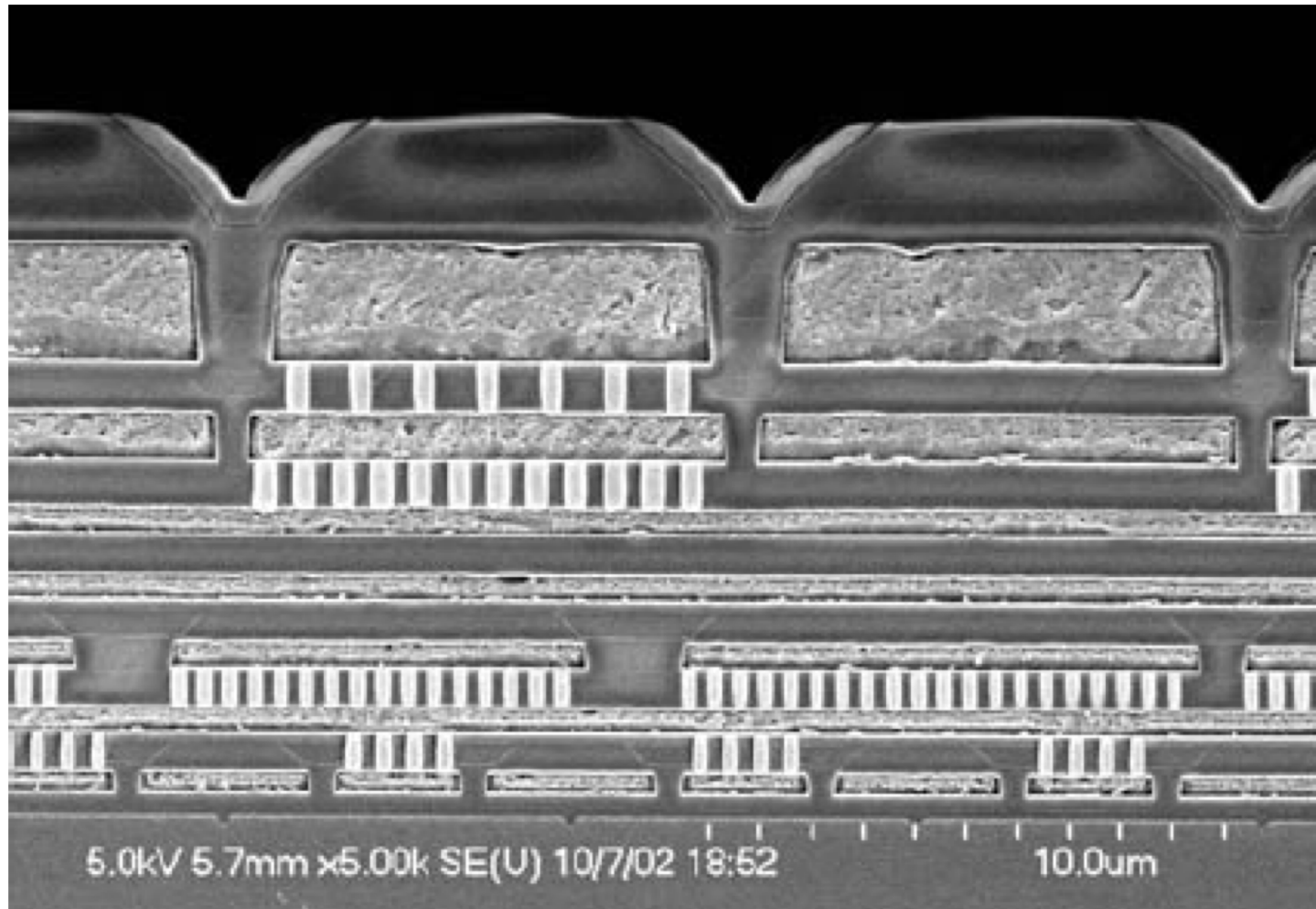


Final wafer product after polishing, cleaning and inspection

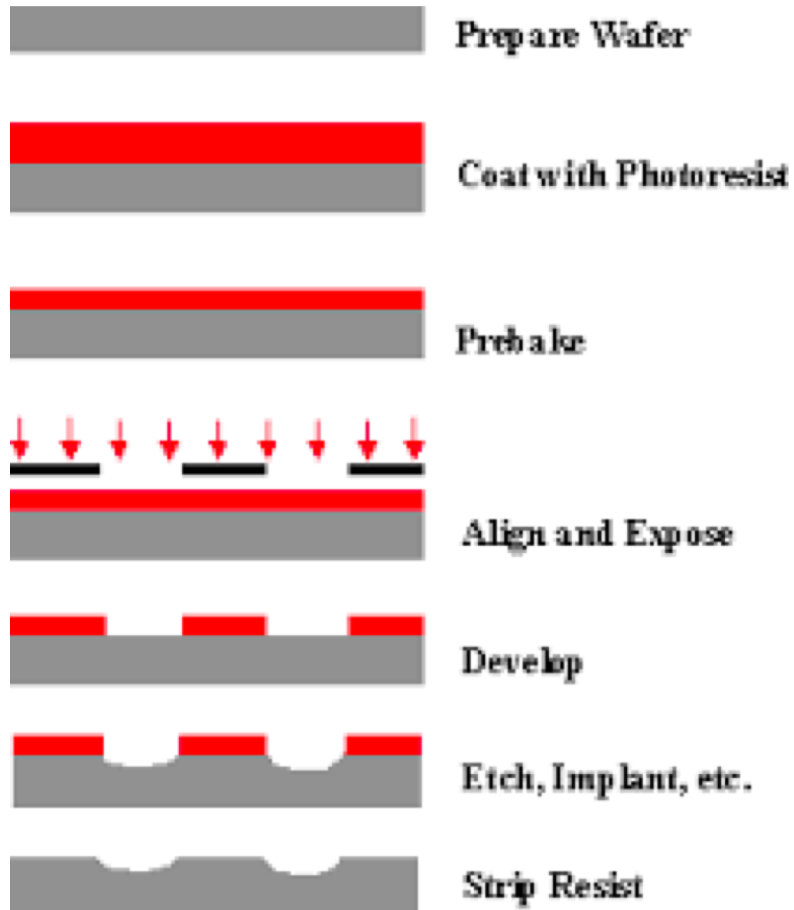


A silicon wafer fabricated with microelectronic circuits

Processed Silicon Wafer Cross-Section



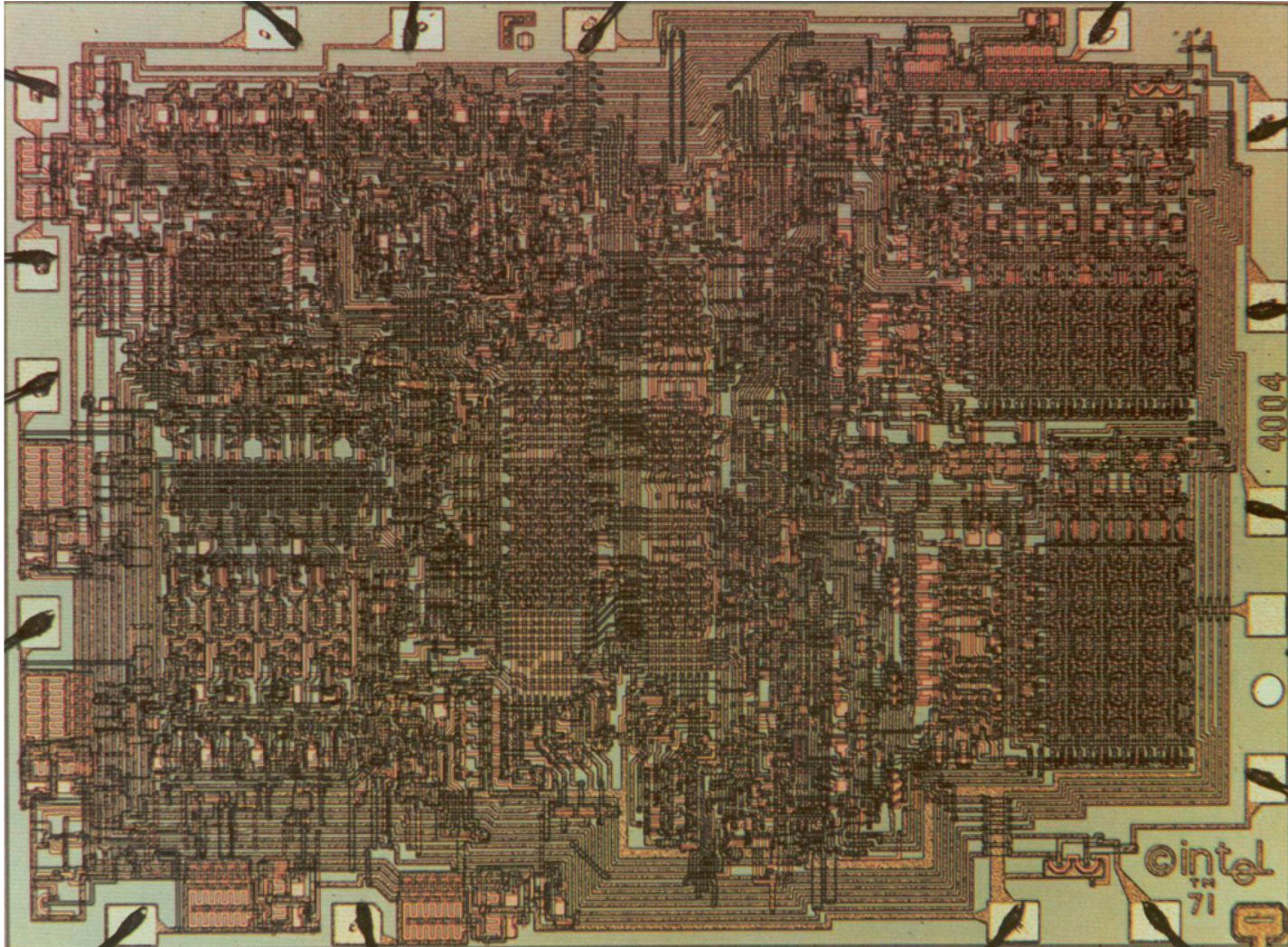
Lithography



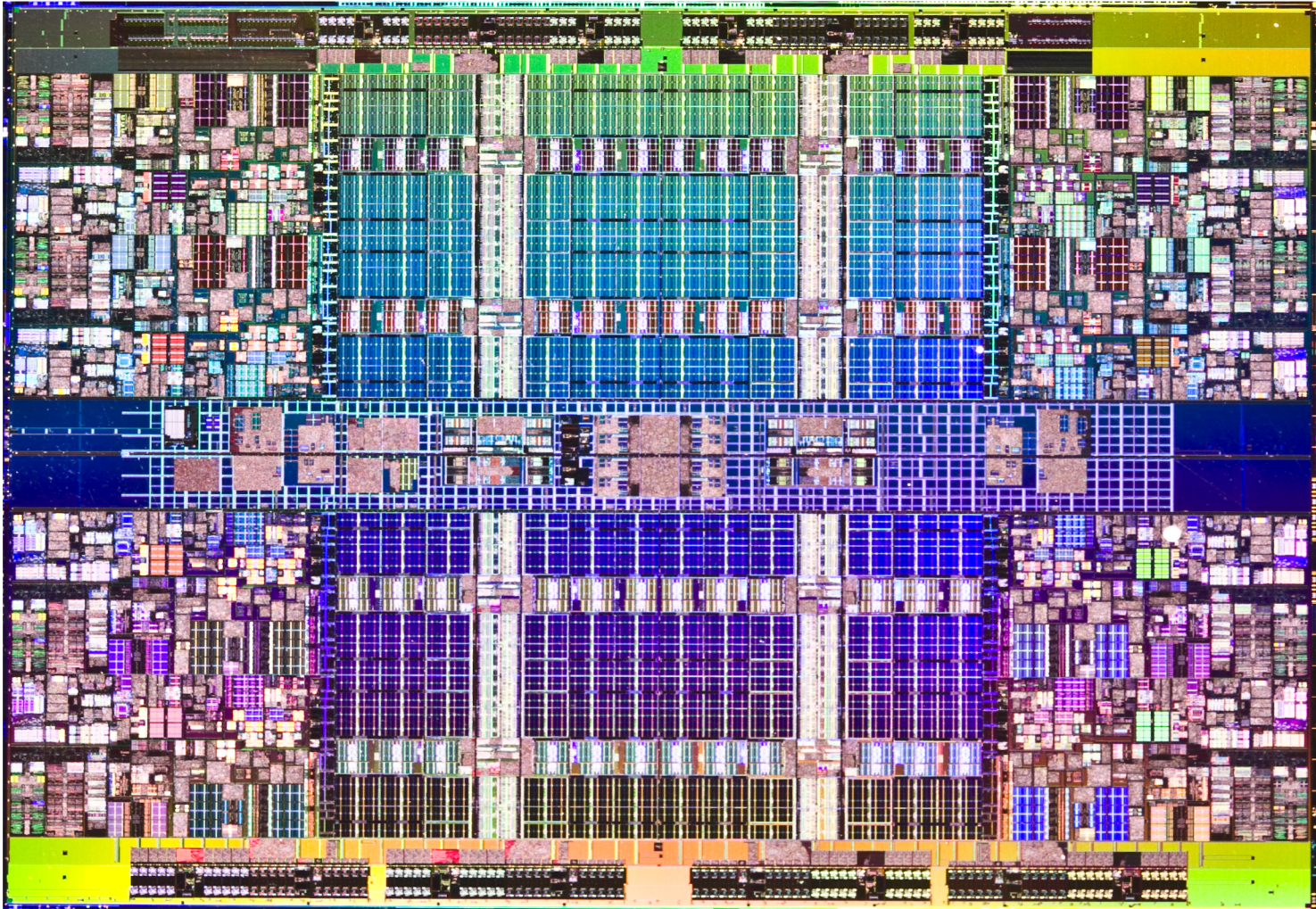
Example 1: XTR Junctions

Example 2: Interconnect

Result



More of same ...



Silicon as a Mechanical Material

KURT E. PETERSEN, MEMBER, IEEE

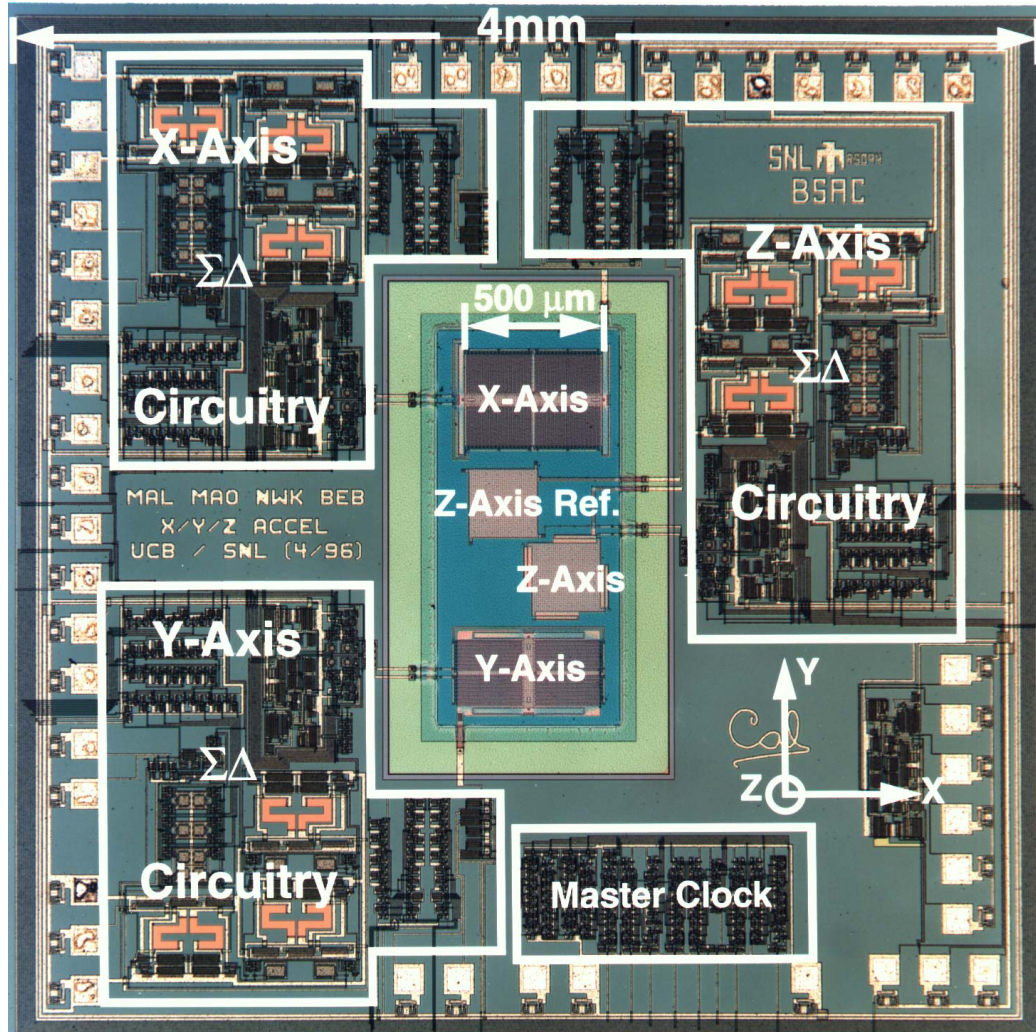
Abstract-Single-crystal silicon is being increasingly employed in a variety of new commercial products not because of its well-established electronic properties, but rather because of its excellent mechanical properties. In addition, recent trends in the engineering literature indicate a growing interest in the use of silicon as a mechanical material with the ultimate goal of developing a broad range of inexpensive, batch-fabricated, high-performance sensors and transducers which are easily interfaced with the rapidly proliferating microprocessor. This review describes the advantages of employing silicon as a mechanical material, the relevant mechanical characteristics of silicon, and the processing techniques which are specific to micromechanical structures. Finally, the potentials of this new technology are illustrated by numerous detailed examples from the literature. It is clear that silicon will continue to be aggressively exploited in a wide variety of mechanical applications complementary to its traditional role as an electronic material. Furthermore, these multidisciplinary uses of silicon will significantly alter the way we think about all types of miniature mechanical devices and components.

I. INTRODUCTION

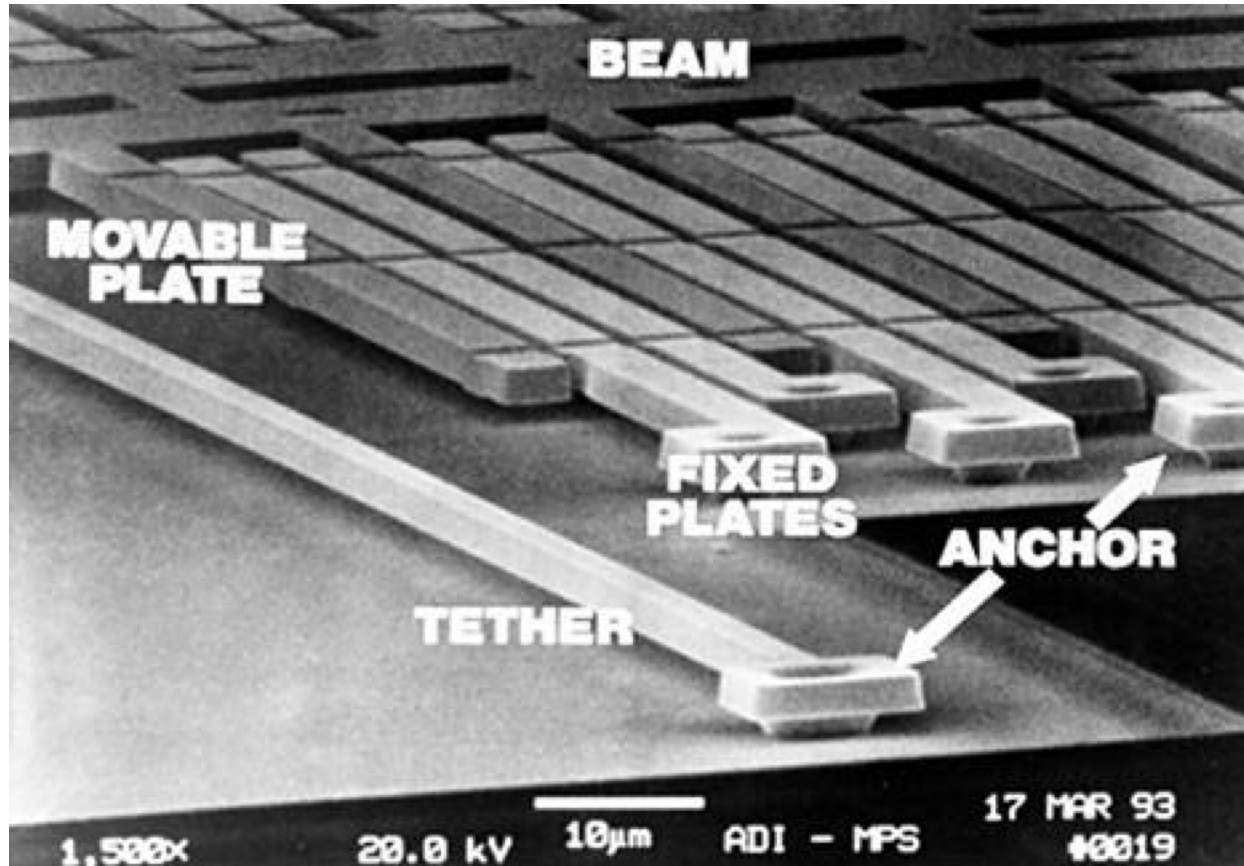
miniaturized mechanical devices and components must be integrated or interfaced with electronics such as the examples given above.

The continuing development of silicon micromechanical applications is only one aspect of the current technical drive toward miniaturization which is being pursued over a wide front in many diverse engineering disciplines. Certainly silicon microelectronics continues to be the most obvious success in the ongoing pursuit of miniaturization. Four factors have played crucial roles in this phenomenal success story: 1) the active material, silicon, is abundant, inexpensive, and can now be produced and processed controllably to unparalleled standards of purity and perfection; 2) silicon processing itself is based on very thin deposited films which are highly amenable to miniaturization; 3) definition and reproduction of the device shapes and patterns are performed using photographic techniques which have also, historically, been capable of high

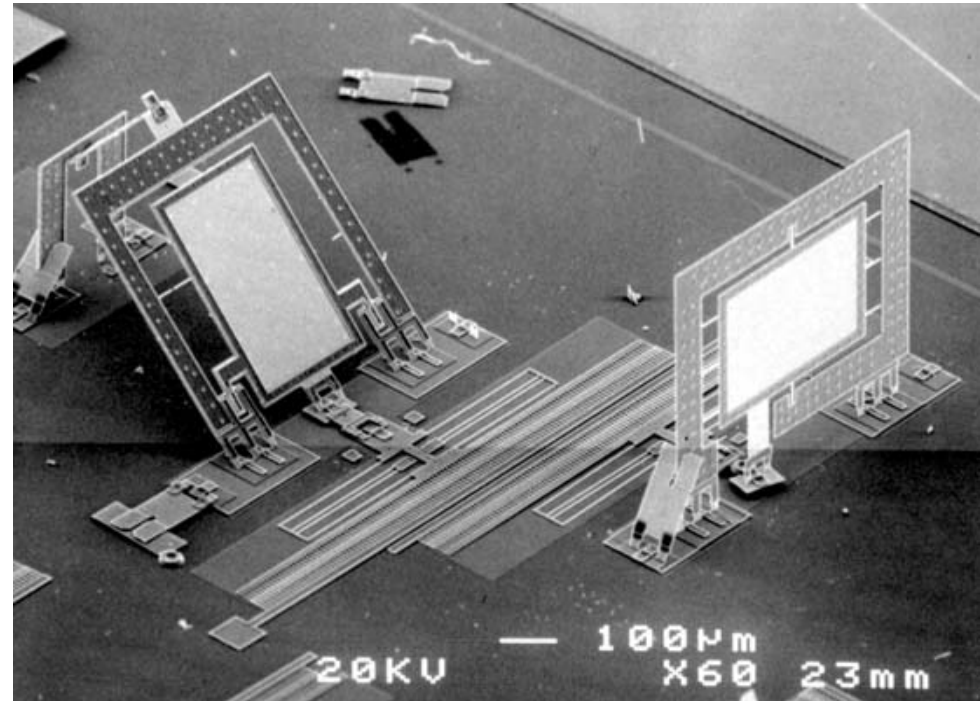
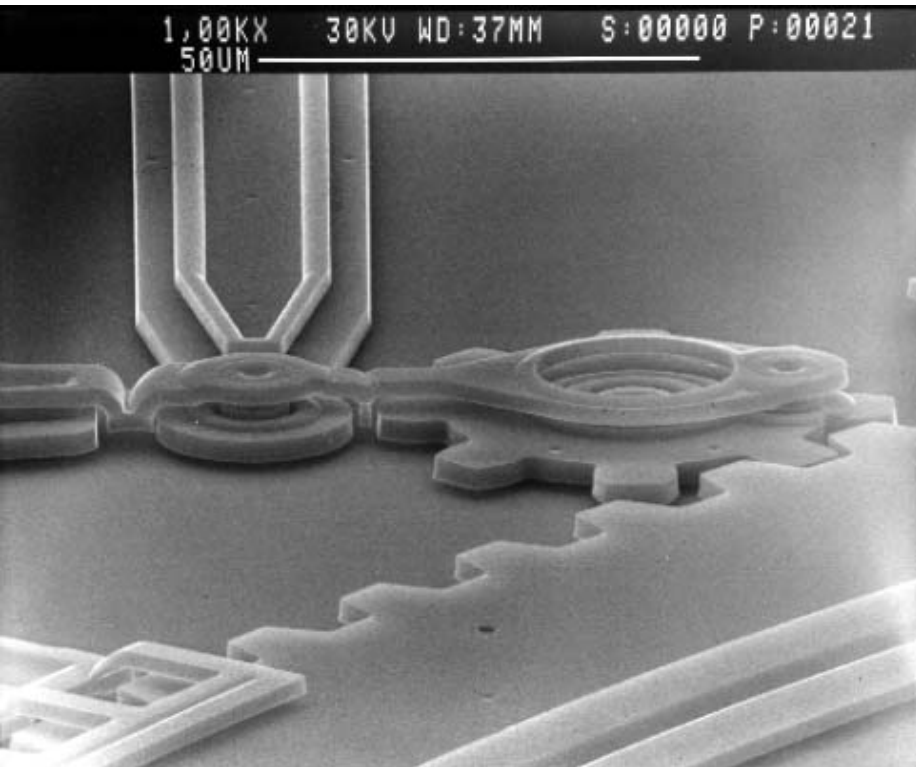
MEMS



MEMS Acceleration Sensor



Gears? 3D?



MEMS Process (Example)
